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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

Complete if Known	
Application Number	10/582,392
Filing Date	June 28, 2007
First Named Inventor	Horsky et al.
Group Art Unit	2821
Examiner Name	Bernard Souw
Attorney Docket Number	211843-00044

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. [1]	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	A1	5,497,006	03-05-1996	Sferlazzo	
	A2	2008-0121811	05-29-2008	Horsky	
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Examiner Initials*	Cite No. [1]	Foreign Patent Document: Country Code [3] –Number [4]– Kind Code [5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T [6]
	B1	WO 2005/059942 A2				
	B2	WO 2004/003973 A3				

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. [1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher city and/or country where published	T [2]
	C1	E.J. Collart et al. "Co-Implantation with Conventional Spike Anneal Solutions for 45 nm Ultra-Shallow Junction Formation", Proceedings of the Eight International Workshop on: Fabrication, Characterization and Modeling Of Ultra-Shallow Doping Profiles in Semiconductors, June 2005, p. 327	
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	C3	L. S. Robertson et al., "The Effect of Impurities and Activation of Ion Implanted boron in Silicon", Mat. Res. Soc. Symp. Vol. 610, pp. B5.8.1-B5.8.6 (2000)	
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Examiner Signature	/Bernard Souw/	05/26/2010

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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